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09/511,592

APPLICANT

Tatau NISHINAGA

FILING DATE

February 23, 2000

GROUP

1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MAA	6 3 9 9 4 7 3	06/2002	Fischer et al.			
MAA	4 1 7 1 2 3 4	10/1979	Nagata et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO
6 1 2 7 1 8 1 7	12/1986	JP			Abstract
1 9 7 2 9 1 8 6	01/1999	DE			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

German Office Action dated June 21, 2004 with English translation.

H. GOSSNER, et al.; "Self-Organizing Growth of Nanometer Mesa Structures on Silicon (100) Substrates", Jpn. J. Appl. Phys. Vol. 33 (1994) pp. 2268-2271, Part 1, No. 4B, April 1994.

B-Y. TSAUR, et al.; "Low-dislocation-density GaAs epilayers grown on Ge-coated Si substrates by means of lateral epitaxial overgrowth", Appl. Phys. Lett. 41(4), 15 August 1982, pp. 347-349.

Y. MATSUNAGA, et al.; "Microchannel Epitaxy of GaAs ON Si(100) Substrates Using SiO₂ Shadow Masks", Electrochemical Society Proceedings Volume 97-21 (1997), pp. 184-188.

EXAMINER

DATE CONSIDERED

1/21/05

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.